

Tunnel contacts JFETs

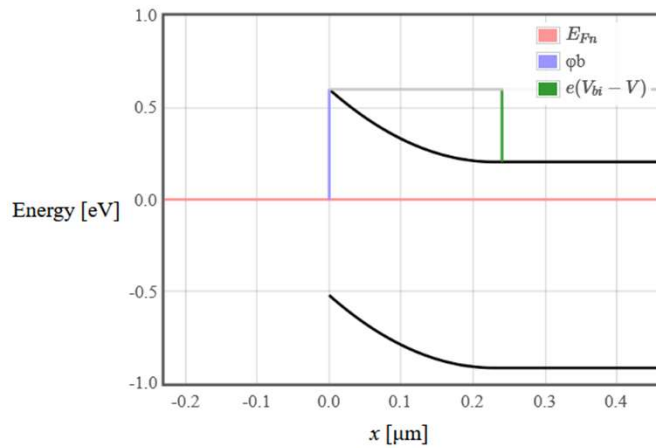
Schottky barrier

$\phi_b = 0.6$ eV
 $E_g = 1.166 - 4.73E-4 * T * T / (T + 636)$ eV
 $N_D = 1E15$ 1/cm³
 $N_c(300) = 2.78E19$ 1/cm³
 $T = 300$ K
 $\epsilon_r = 12$
 $V = -0.5$ V

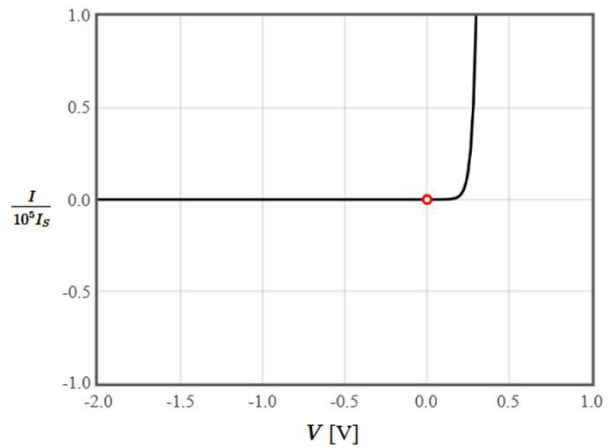
$E_g = 1.12$ eV $W = 1.05$ μm $V_{bi} = 0.335$ V $C_j = 10.1$ nF/cm²

$$E = \frac{eN_D}{\epsilon_r \epsilon_0} (x - x_n)$$

Band diagram

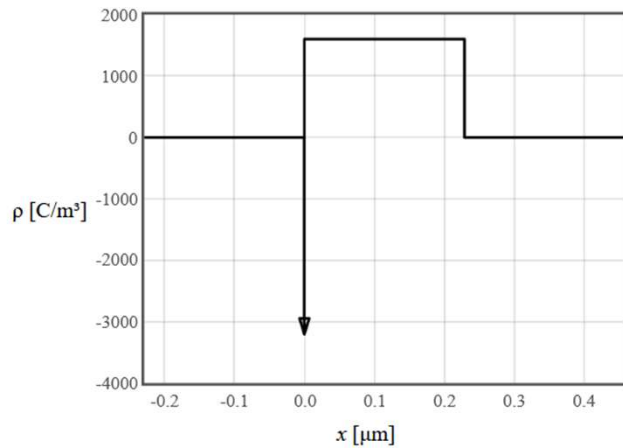


Current-Voltage Characteristics

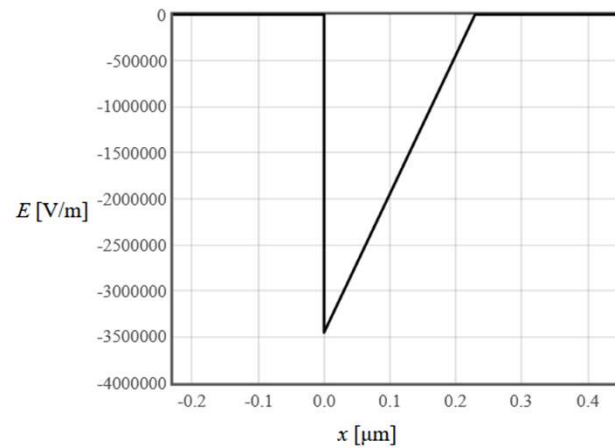


$$W \approx x_n = \sqrt{\frac{2\epsilon(V_{bi} - V)}{eN_D}}$$

Charge density



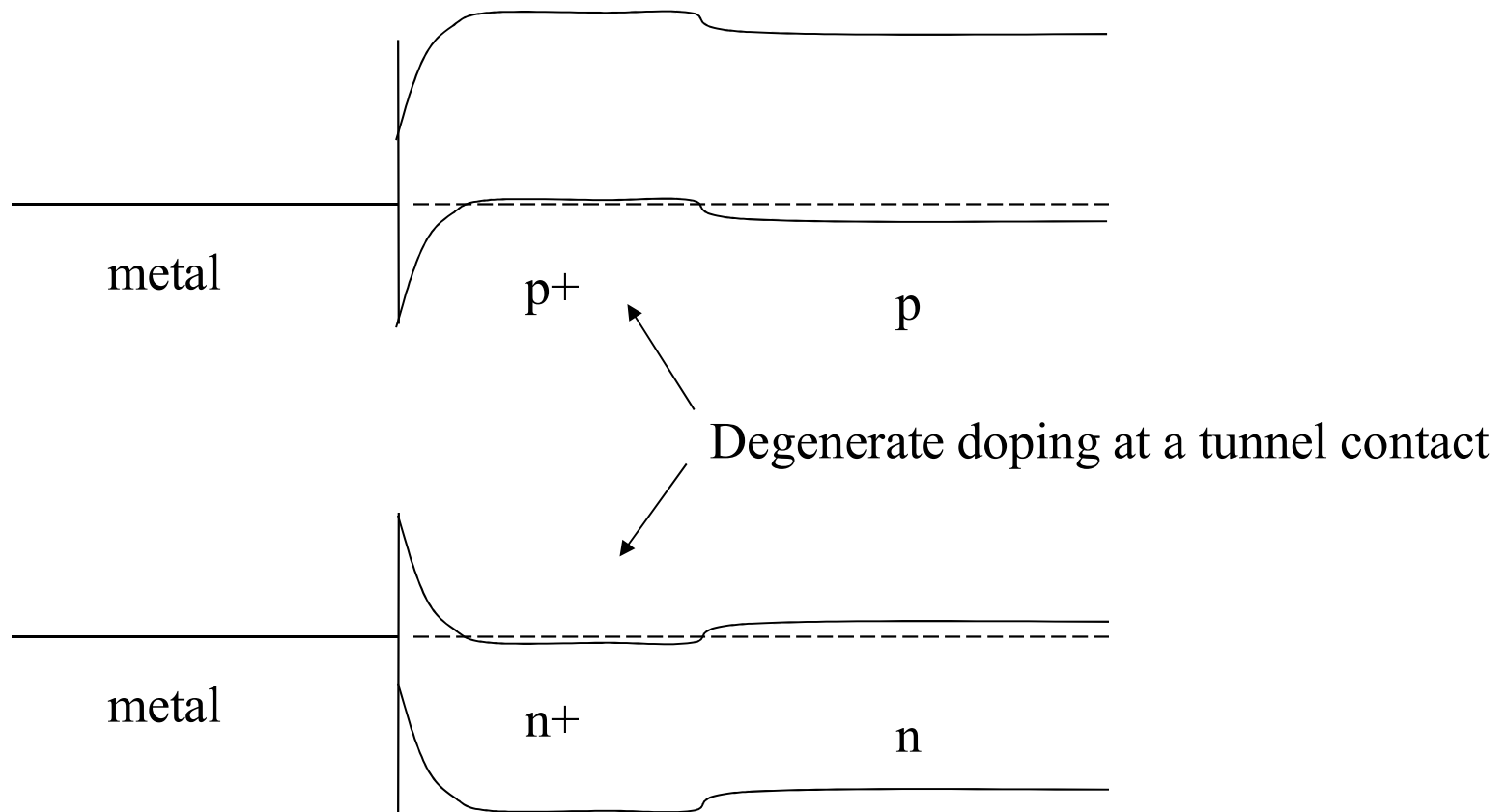
Electric field



$$V = \frac{-eN_D}{\epsilon} \left(\frac{x^2}{2} - xx_n \right)$$

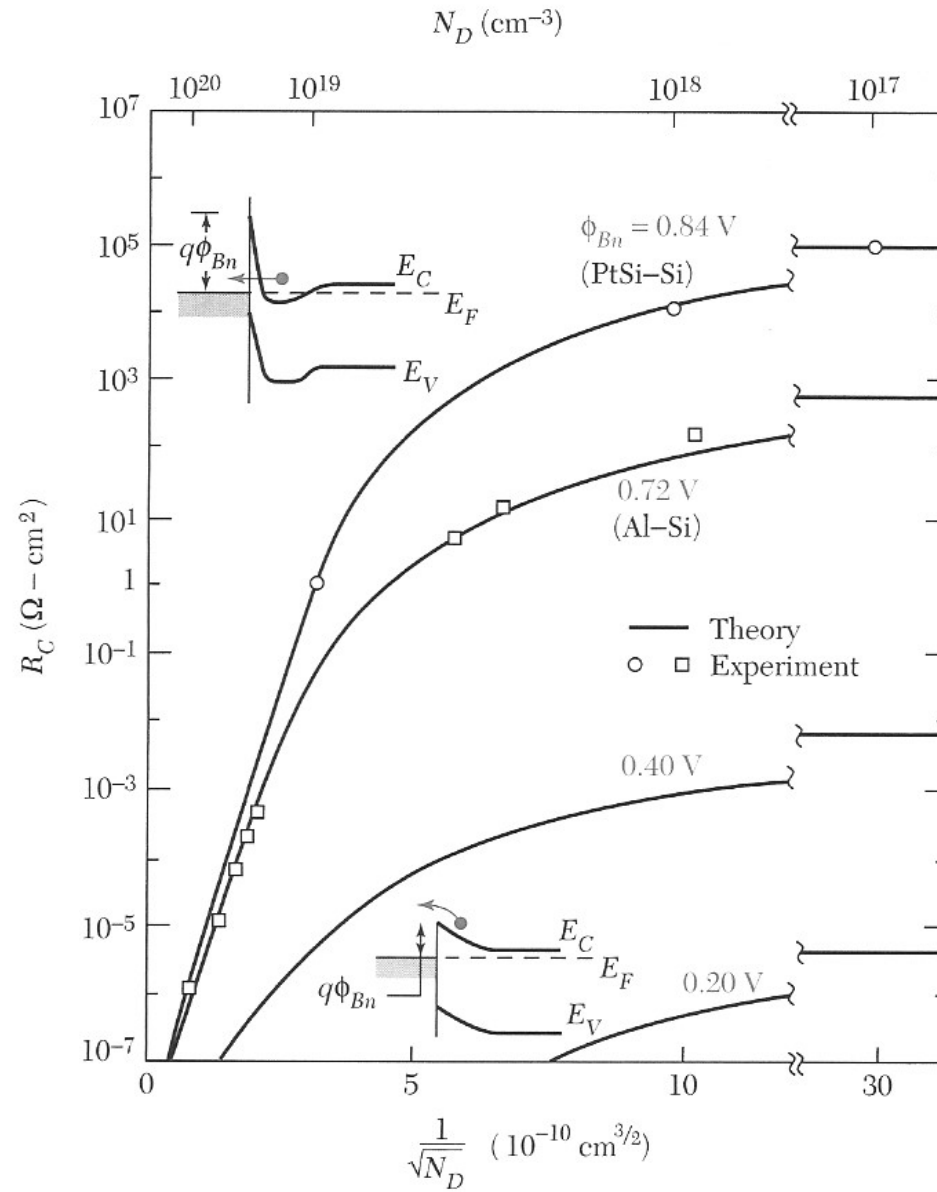
Tunnel contacts

For high doping, the Schottky barrier is so thin that electrons can tunnel through it.



Tunnel contacts have a linear resistance.

Contacts



Transport mechanisms

Drift

Diffusion

Thermionic emission

Tunneling

All mechanisms are always present.

One or two transport mechanisms can dominate depending on the device and the bias conditions.

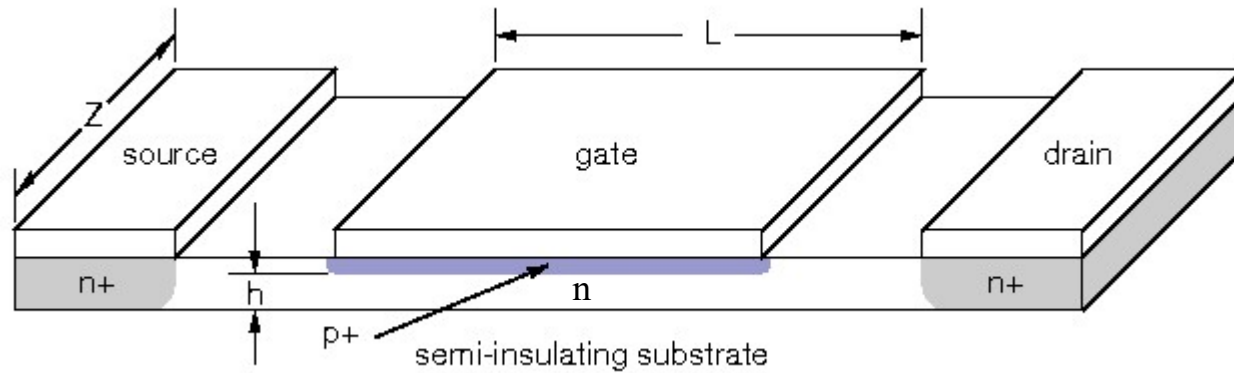
In a forward biased pn-junction, diffusion dominates.

In a tunnel contact, tunneling dominates.

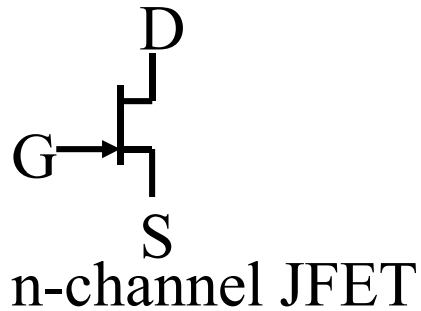
In a Schottky diode, thermionic emission dominates.

Junction Field Effect Transistors (JFETs)

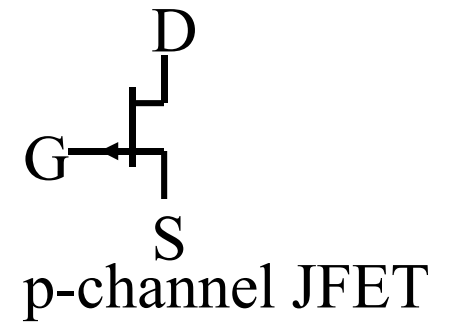
JFET



n-channel JFET



$$x_n = \sqrt{\frac{2\epsilon(V_{bi} - V)}{eN_D}}$$

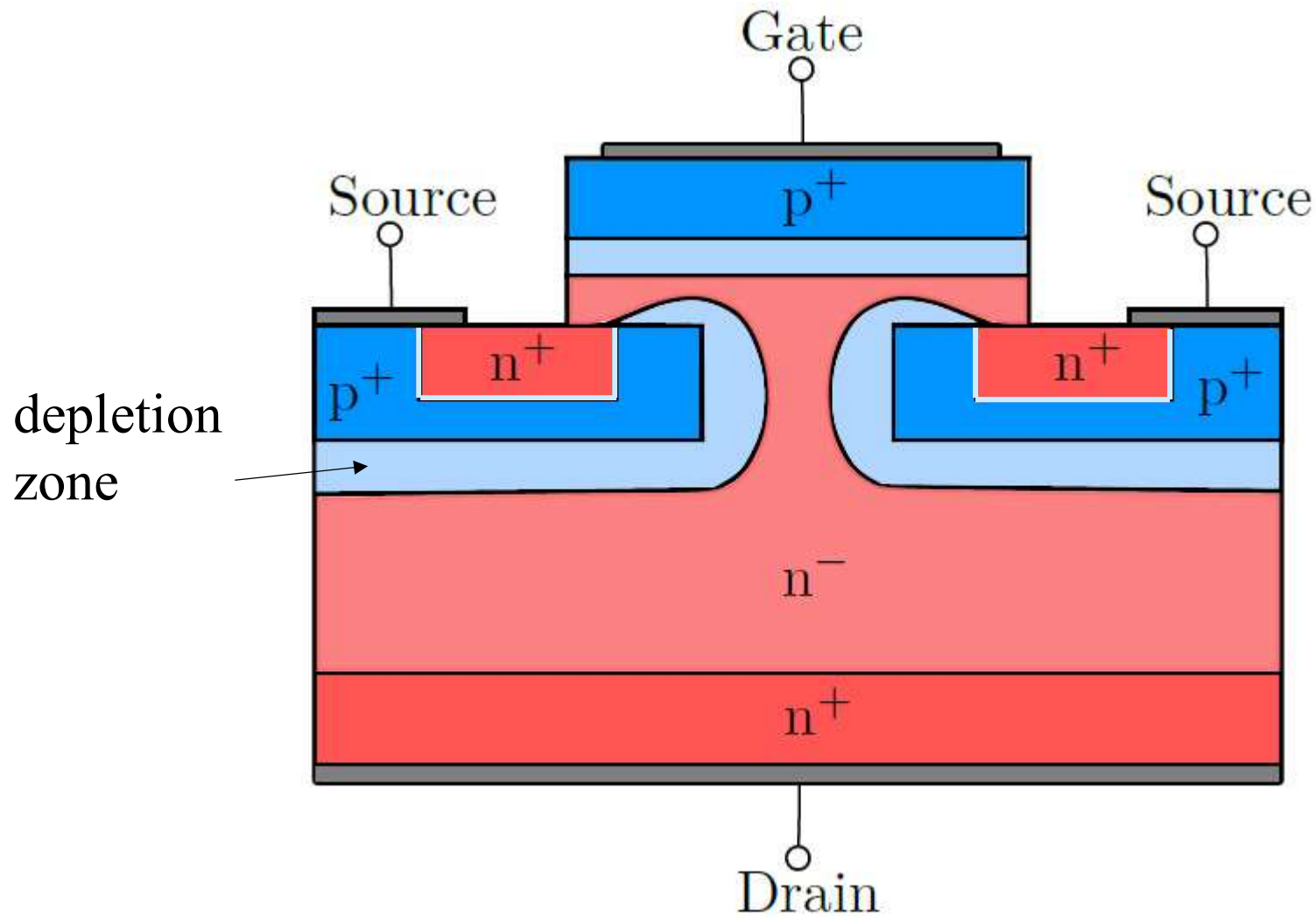


Pinch-off at $h = x_n$

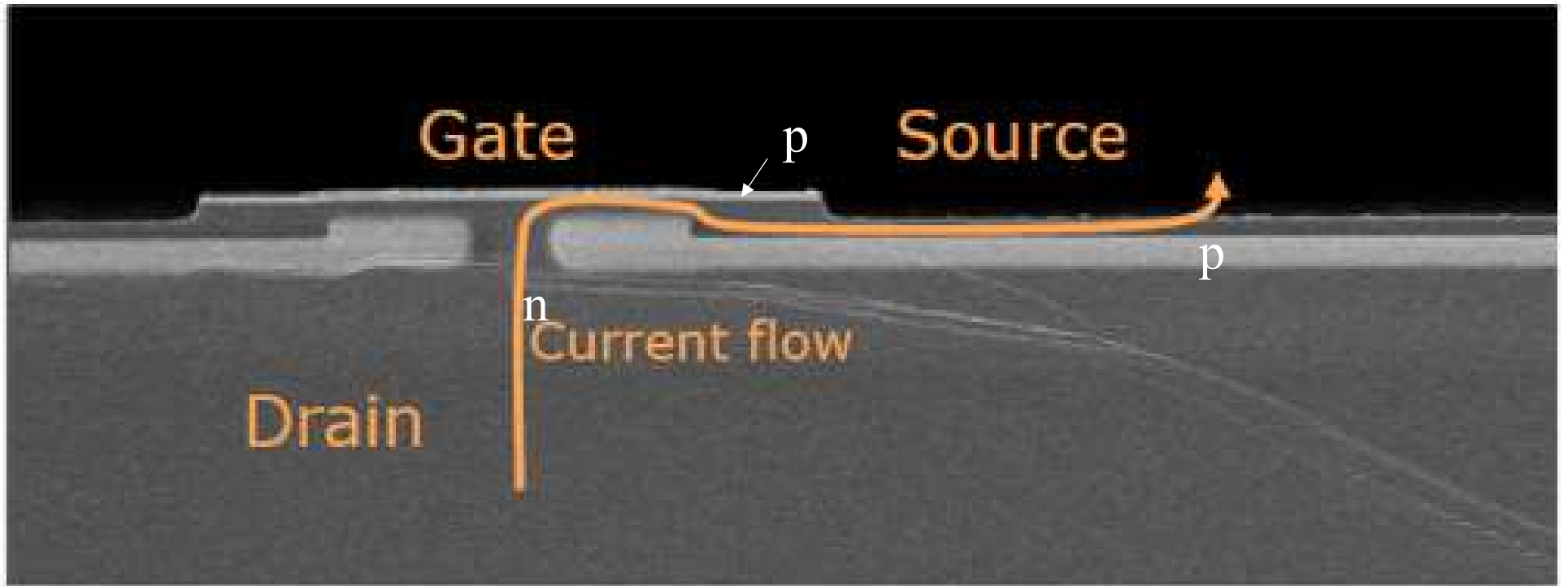
At Pinch-off,
$$V = V_{bi} - \frac{eN_D h^2}{2\epsilon}$$

$$V_p = \frac{eN_D h^2}{2\epsilon}$$

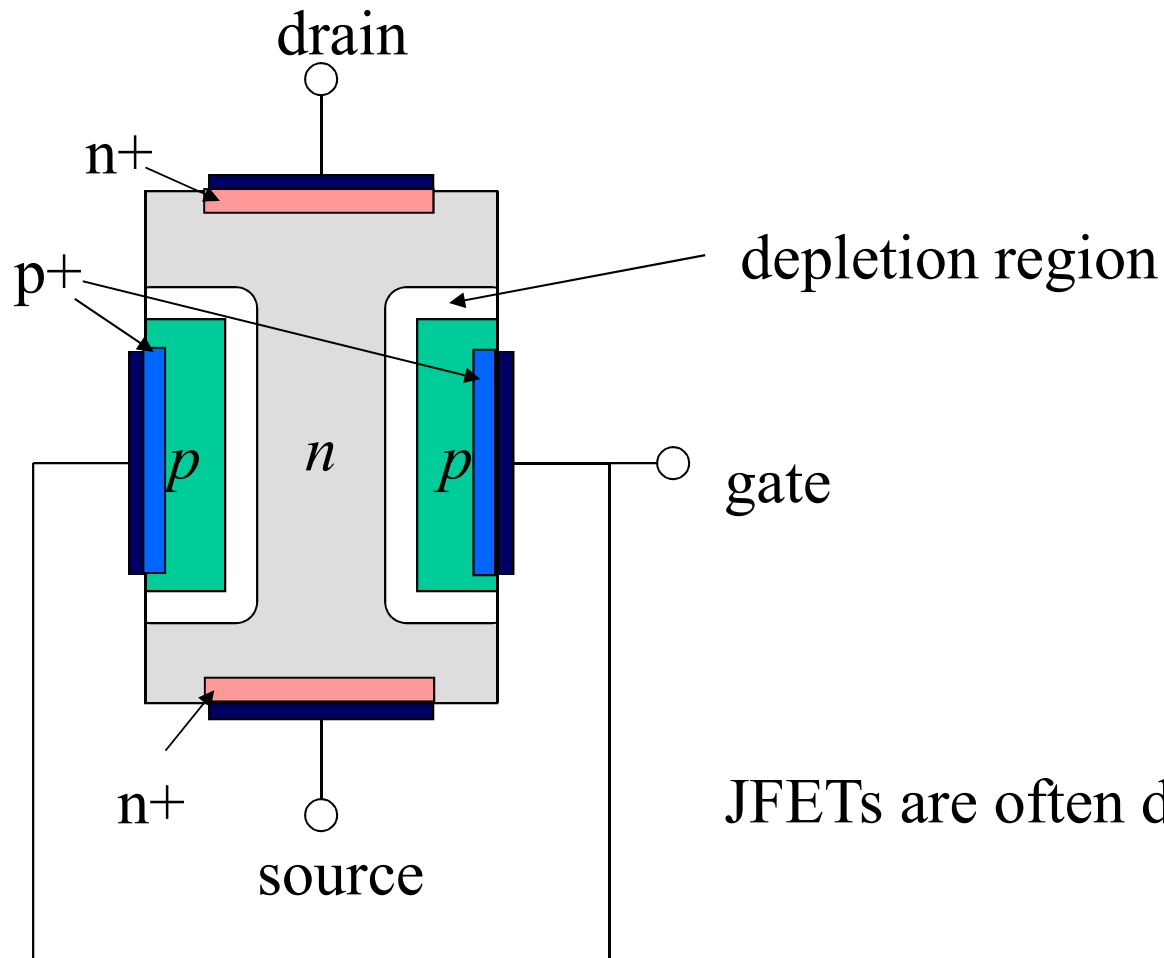
n-channel (power) JFET



Power SiC JFET



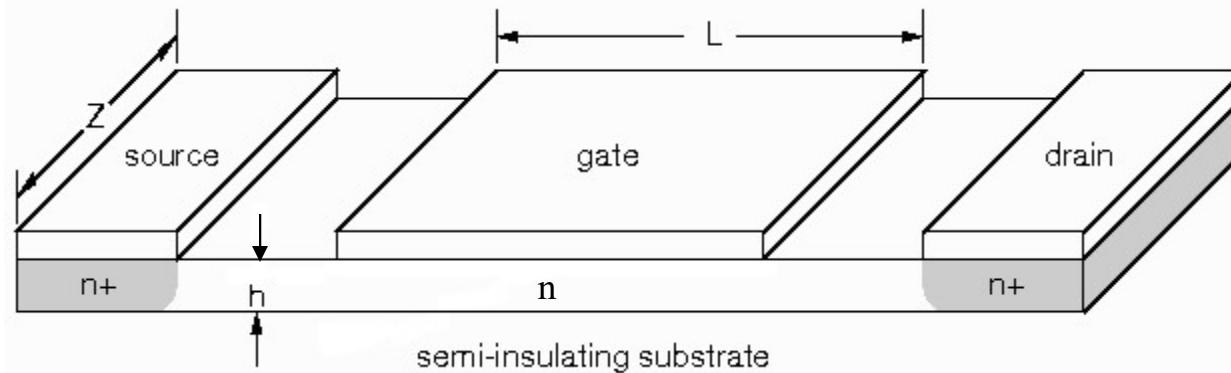
n-channel JFET



JFETs are often discrete devices

MESFET

Metal-Semiconductor Field Effect Transistors

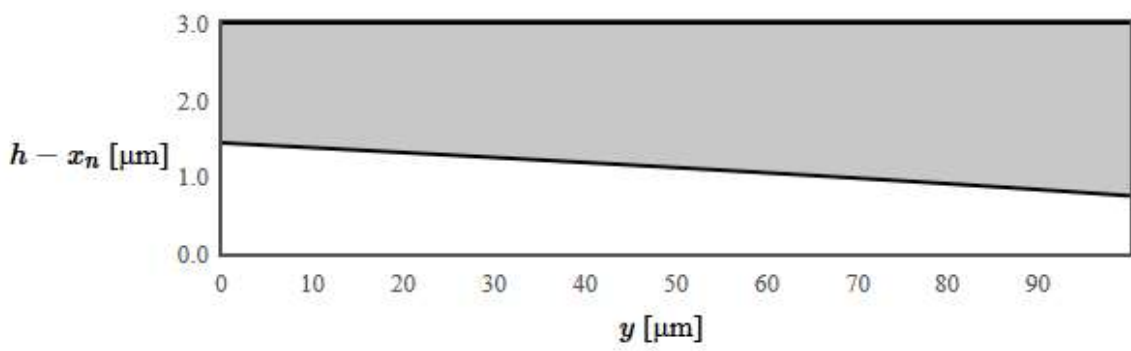
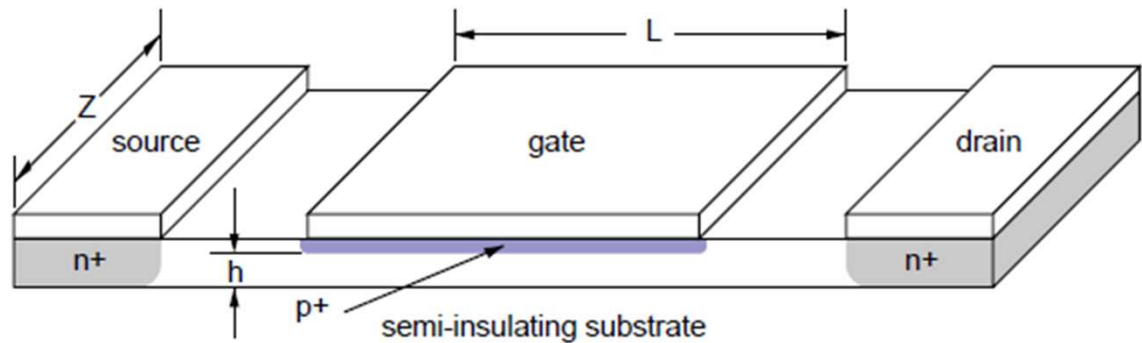


Depletion layer created by Schottky barrier

$$x_n = \sqrt{\frac{2\epsilon(V_{bi} - V)}{eN_D}}$$

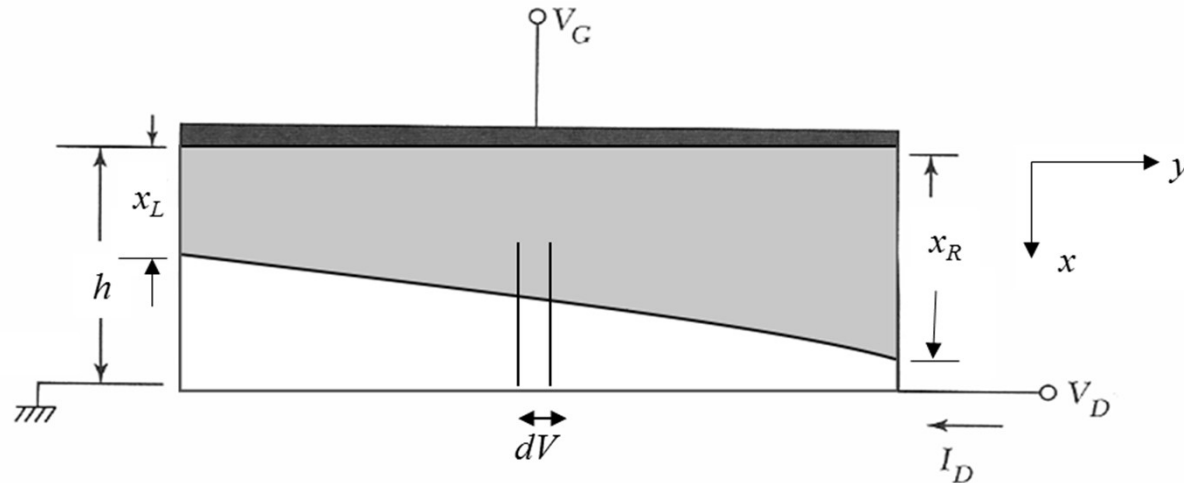
Fast transistors can be realized in n-channel GaAs, however GaAs has a low hole mobility making p-channel devices slower.

JFET Gradual Channel Approximation



$N_c(300K) = 2.78E19 \text{ cm}^{-3}$
 $N_v(300K) = 9.84E18 \text{ cm}^{-3}$
 $E_g = 1.166 - 4.73E-4 * T * T / (T + 636) \text{ eV}$
 $N_D = 1E15 \text{ cm}^{-3}$
 $N_A = 1E19 \text{ cm}^{-3}$
 $\mu_n = 1350 \text{ cm}^2/Vs$
 $h = 3 \text{ }\mu\text{m}$
 $L = 100 \text{ }\mu\text{m}$
 $Z = 100 \text{ }\mu\text{m}$
 $\epsilon_r = 11.9$
 $T = 300 \text{ K}$
 $V_D = 2 \text{ V}$
 $V_g = -1 \text{ V}$

JFET

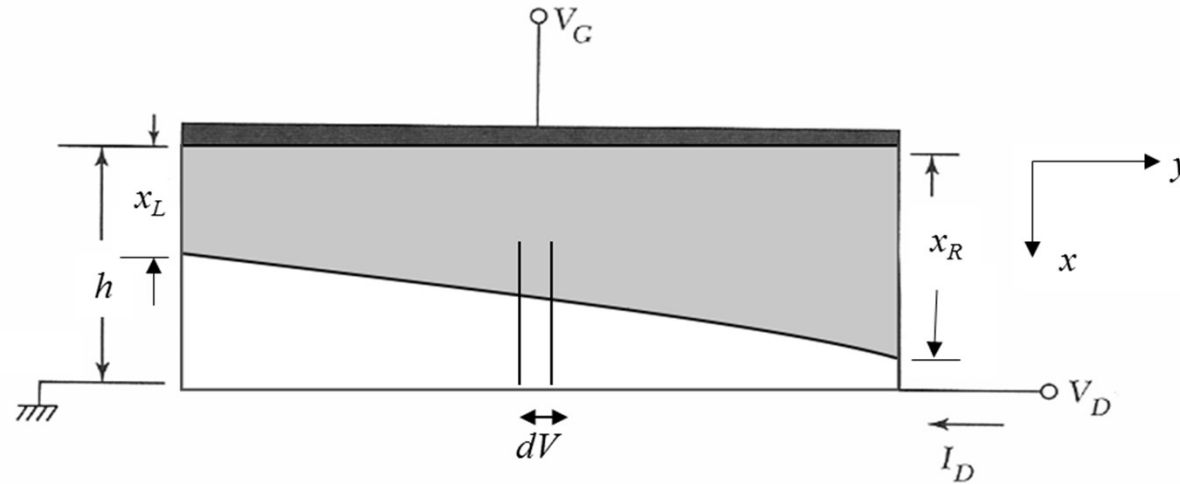


There is a long derivation to determine how the current depends on V_G and V_D .

We will find a relatively simple formula (probably familiar to electrical engineers).

Understanding the derivation is important for knowing when this formula is valid.

JFET



$$dV = I_D dR = I_D \frac{\rho dy}{Z(h - x_n(y))}$$

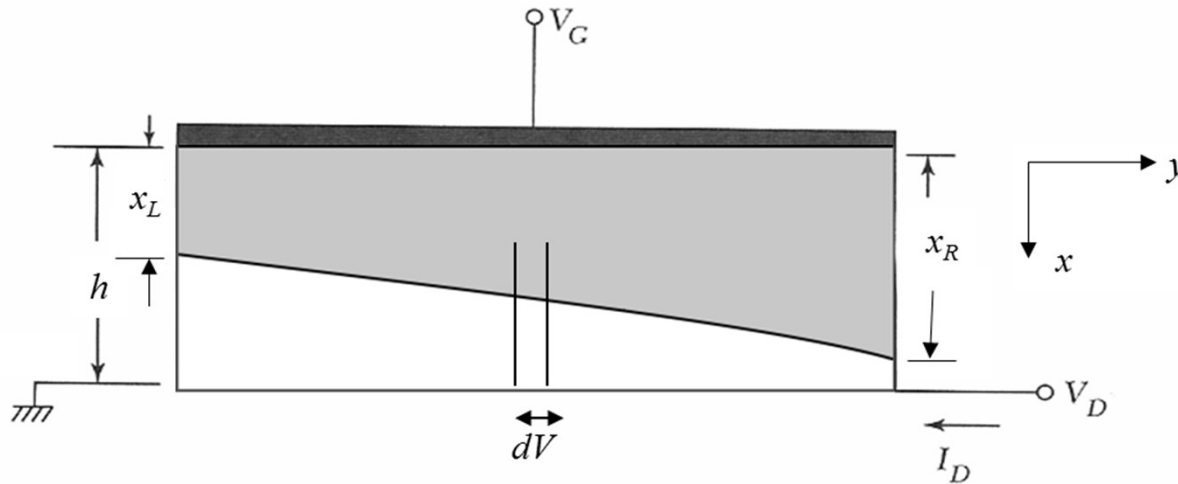
$$\rho = \frac{1}{\sigma} = \frac{1}{ne\mu_n} = \frac{1}{N_D e\mu_n}$$

$$dV = I_D \frac{dy}{e\mu_n N_D Z(h - x_n(y))}$$

I_D is constant throughout the transistor $\longrightarrow I_D dy = e\mu_n N_D Z(h - x_n(y)) dV$

JFET

$$I_D dy = e\mu_n N_D Z (h - x_n(y)) dV$$

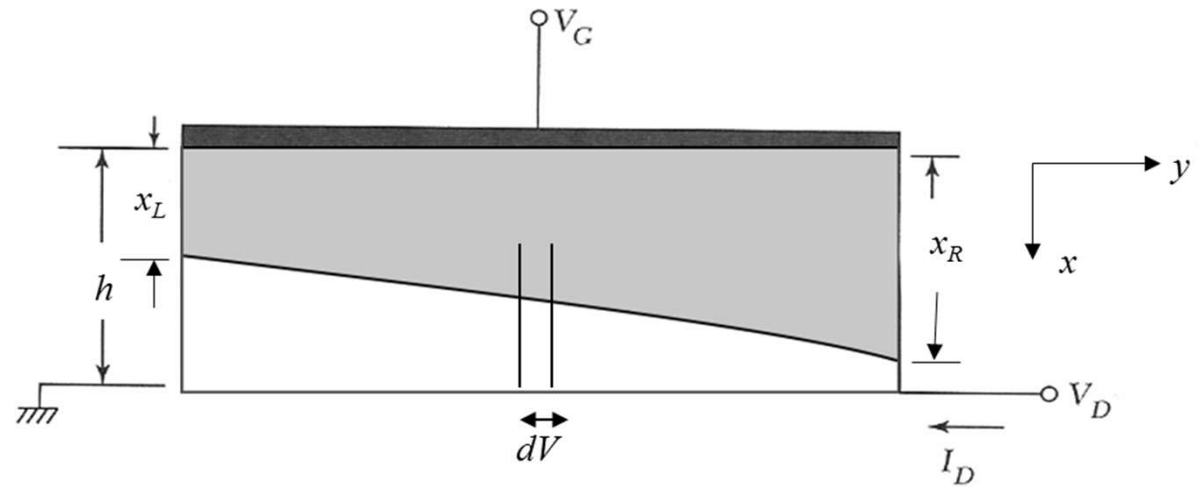


V_G is a forward bias
 $V(y)$ is a reverse bias.

depletion width is a function of position $x_n(y) = \sqrt{\frac{2\epsilon(V_{bi} + V(y) - V_G)}{eN_D}}$

differentiate $\frac{dx_n(y)}{dV} =$

JFET



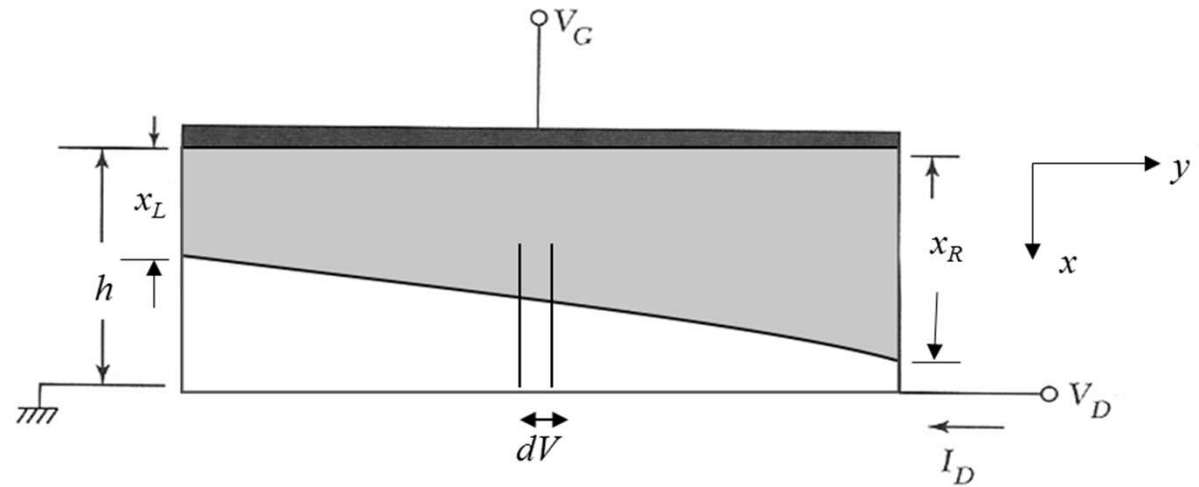
$$I_D dy = e\mu_n N_D Z (h - x_n(y)) dV \quad \leftarrow \text{from last slide}$$

$$dV = \frac{eN_D x_n}{\epsilon} dx_n$$

$$\frac{dx_n(y)}{dy} = \frac{I_D}{e\mu_n N_D Z (h - x_n(y)) \frac{eN_D}{\epsilon} x_n(y)}$$

If I_D is known, this can be solved for $x_n(y)$.

JFET



$$I_D dy = e\mu_n N_D Z (h - x_n(y)) dV \quad \leftarrow \text{from a previous slide}$$

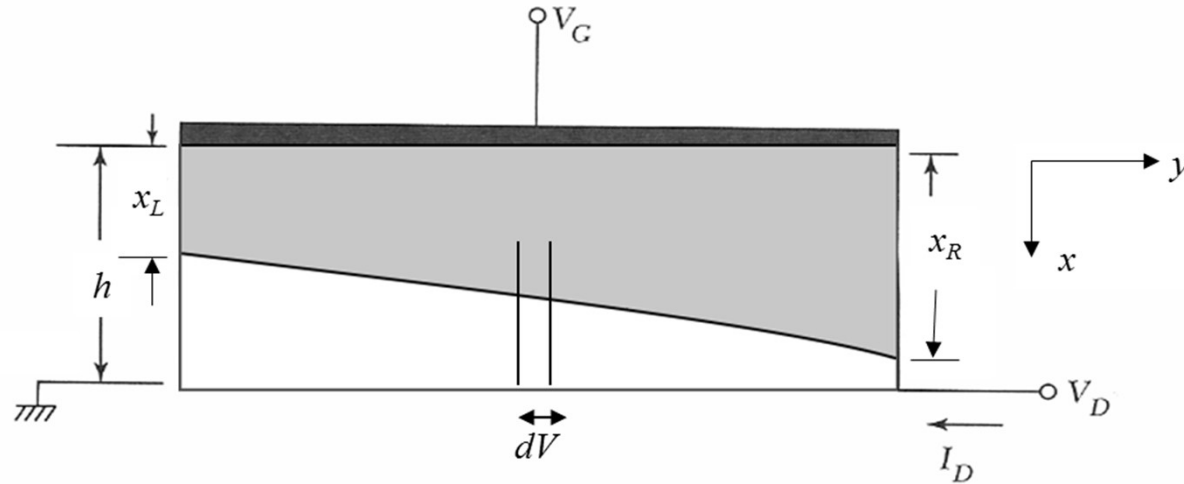
$$dV = \frac{eN_D x_n}{\epsilon} dx_n \quad \leftarrow \text{from a previous slide}$$

$$I_D dy = e\mu_n N_D Z (h - x_n(y)) \frac{eN_D}{\epsilon} x_n dx_n$$

$$I_D \int_0^L dy = e\mu_n N_D Z \frac{eN_D}{\epsilon} \int_{x_L}^{x_R} (h - x_n(y)) x_n dx_n$$

$$I_D = \frac{\mu_n N_D^2 Z e^2}{2L\epsilon} \left[h(x_R^2 - x_L^2) - \frac{2}{3}(x_R^3 - x_L^3) \right]$$

JFET



$$I_D = \frac{\mu_n N_D^2 Z e^2}{2L\epsilon} \left[h(x_R^2 - x_L^2) - \frac{2}{3}(x_R^3 - x_L^3) \right]$$

$$h = \sqrt{\frac{2\epsilon V_p}{eN_D}}$$

$$x_L = \sqrt{\frac{2\epsilon(V_{bi} - V_G)}{eN_D}}$$

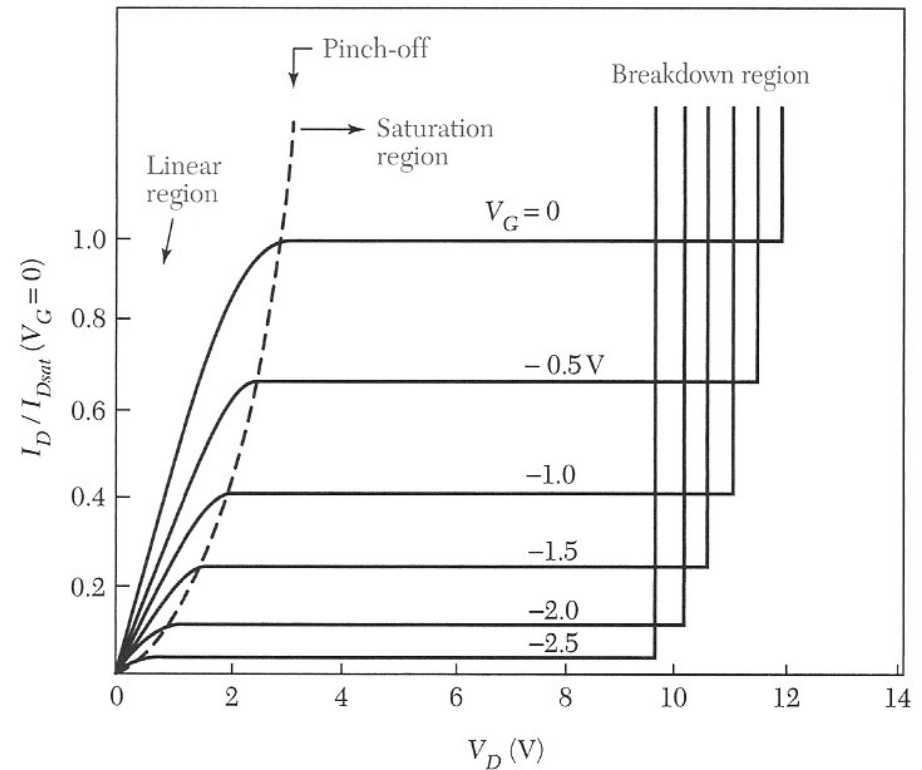
$$x_R = \sqrt{\frac{2\epsilon(V_{bi} - V_G + V_D)}{eN_D}}$$

JFET - drain current

$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

$$I_p = \frac{\mu_n N_D^2 Z e^2 h^3}{2L\epsilon} \quad V_p = \frac{eN_D h^2}{2\epsilon}$$

valid in the linear regime
(until pinch-off)



JFET - Linear regime

$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

In the linear regime $V_D \ll V_{sat}$.

$$\frac{dI_D}{dV_D} =$$

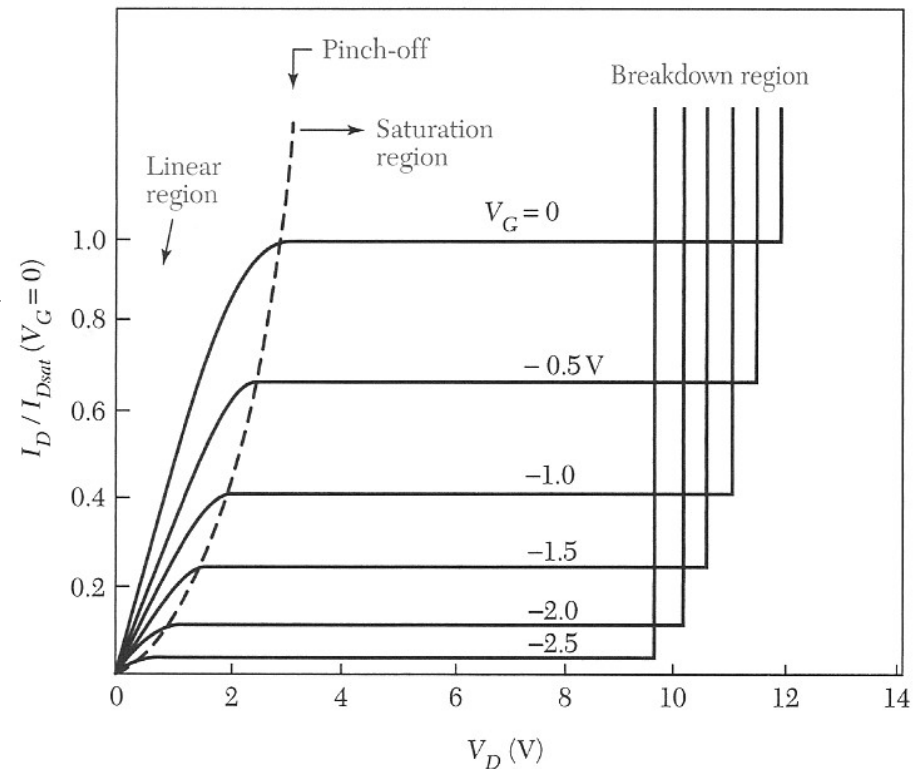
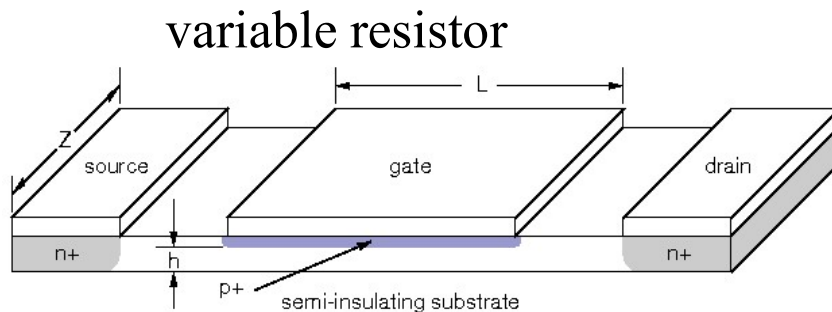
JFET - Linear regime

$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

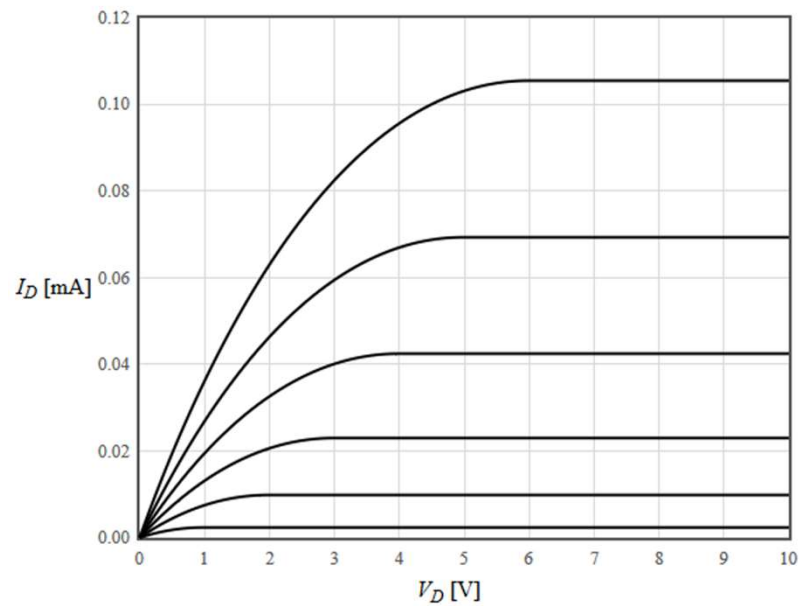
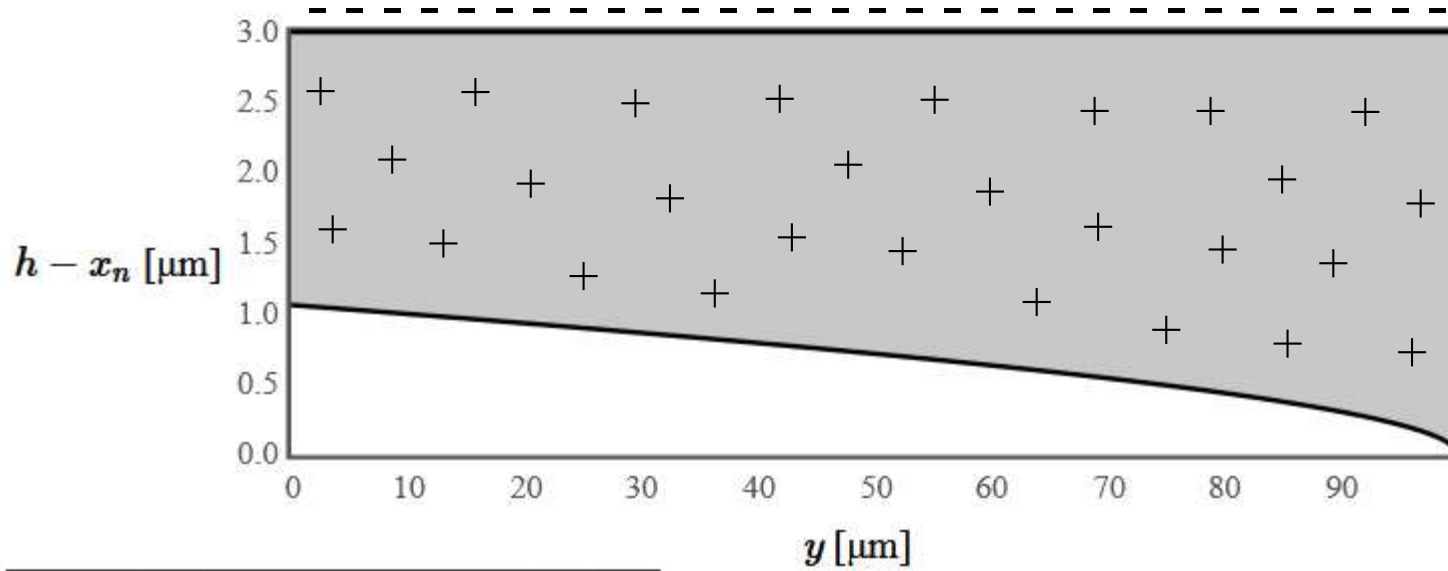
In the linear regime $V_D \ll V_{sat}$.

$$\frac{dI_D}{dV_D} = I_p \left[\frac{1}{V_p} - \frac{1}{V_p} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{1/2} \right]$$

$$I_D \approx \frac{I_p}{V_p} \left[1 - \sqrt{\frac{V_{bi} - V_G}{V_p}} \right] V_D \text{ for } V_D \ll V_{sat}$$

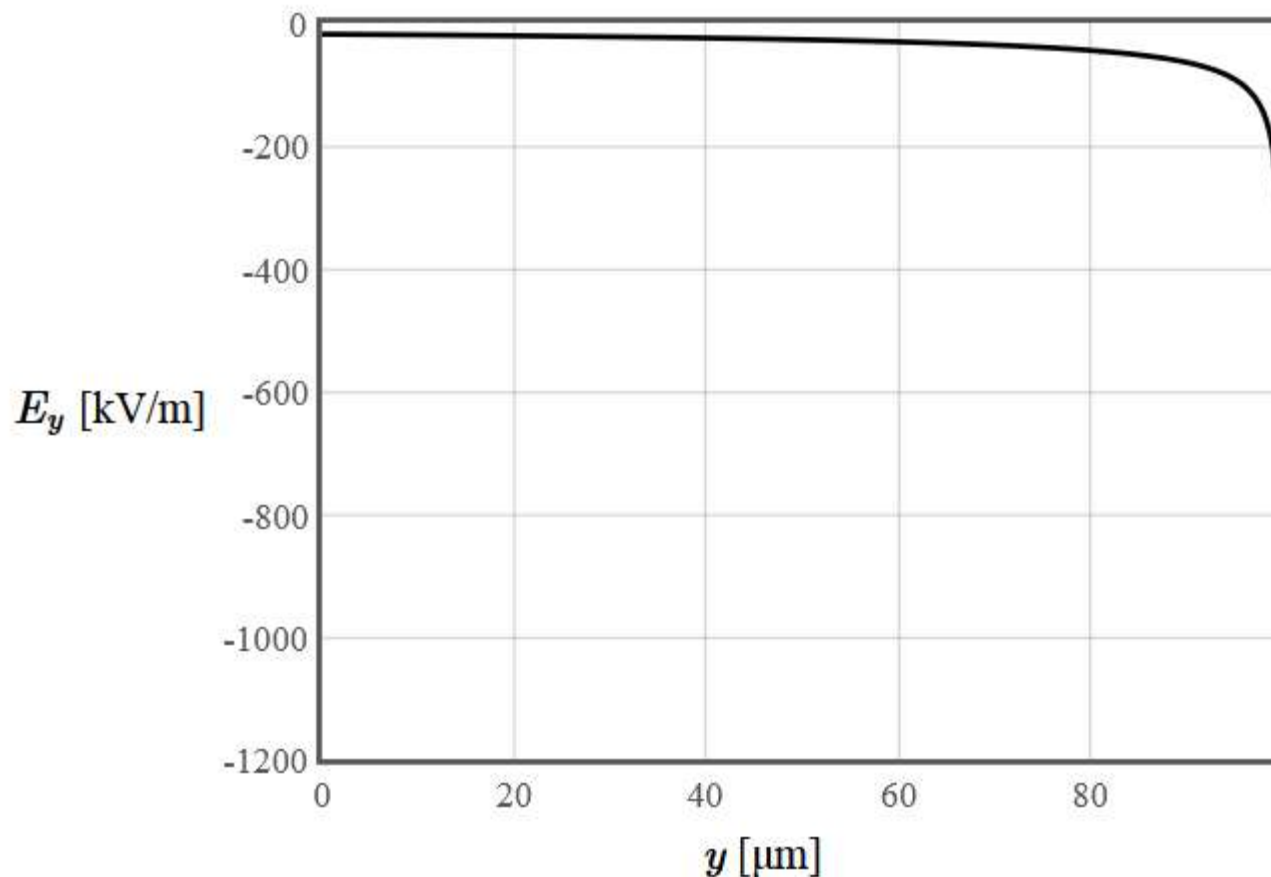


Pinch-off



At Pinch-off, E in gradual channel approximation diverges

$$\nabla \cdot \vec{E} = \frac{dE_x}{dx} + \frac{dE_y}{dy} = \frac{\rho}{\epsilon_r \epsilon_0} = \frac{eN_D}{\epsilon_r \epsilon_0}$$



JFET - Saturation regime

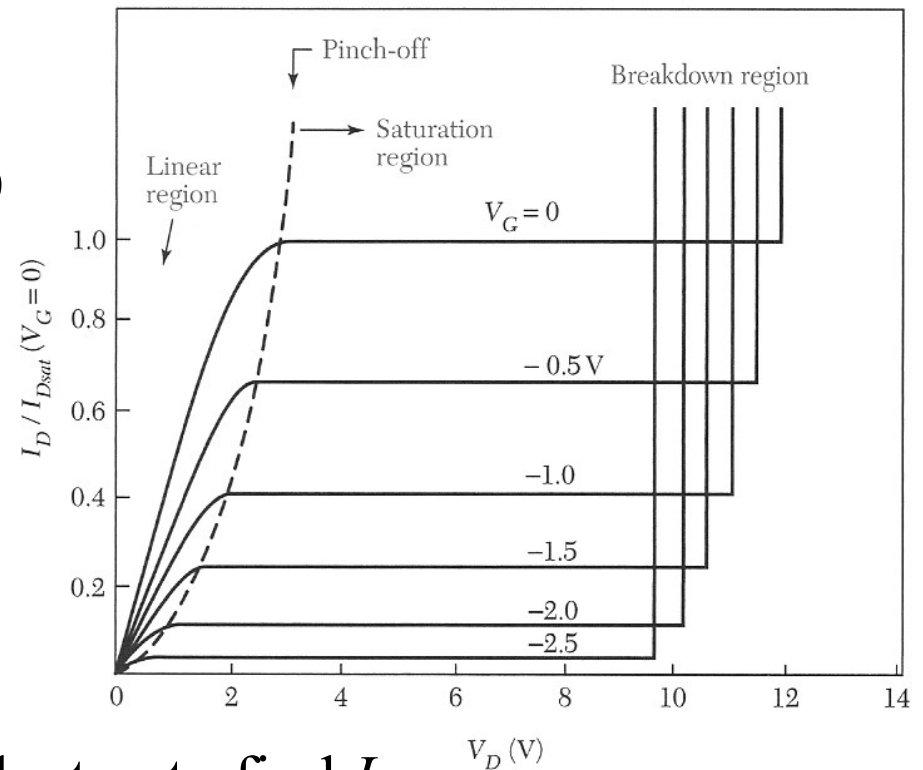
$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

set $dI_D/dV_D = 0$ to find V_{sat}

$$\frac{dI_D}{dV_D} = I_p \left[\frac{1}{V_p} - \frac{1}{V_p} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{1/2} \right] = 0$$

$$dI_D/dV_D = 0 \text{ when } \frac{V_{bi} + V_D - V_G}{V_p} = 1$$

$$V_{sat} = V_p - V_{bi} + V_G$$



Substitute V_{sat} into the equation at the top to find I_{sat}

JFET - Saturation regime

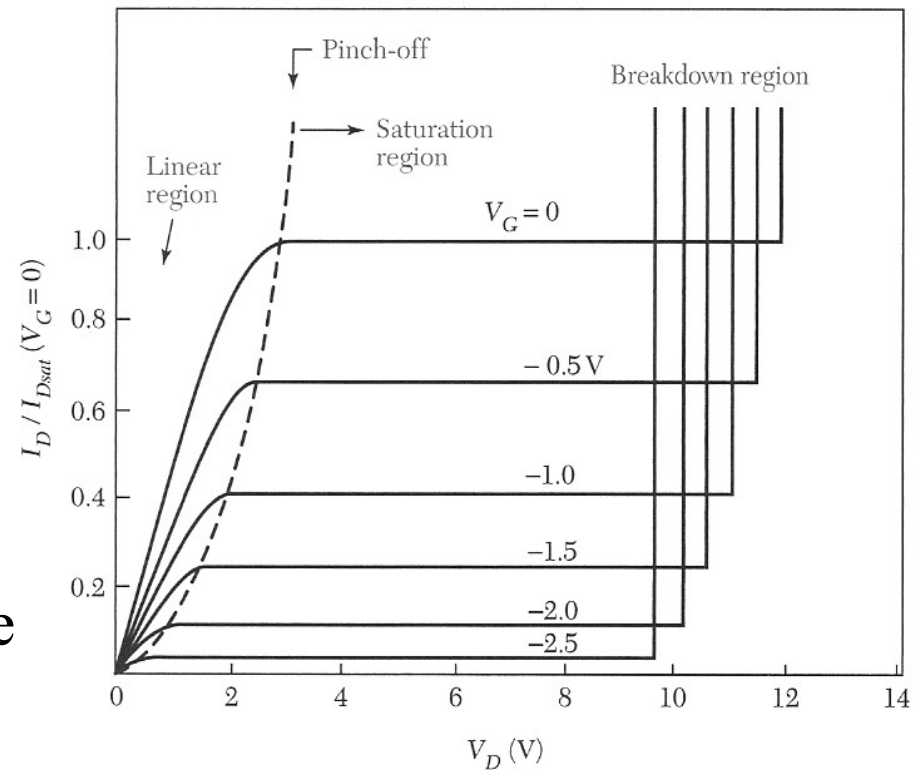
$$V_{sat} = V_p - V_{bi} + V_G$$

$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

$$I_{sat} = I_p \left[\frac{1}{3} - \frac{V_{bi} - V_G}{V_p} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

No V_D dependence

Voltage controlled current source



JFET - transconductance

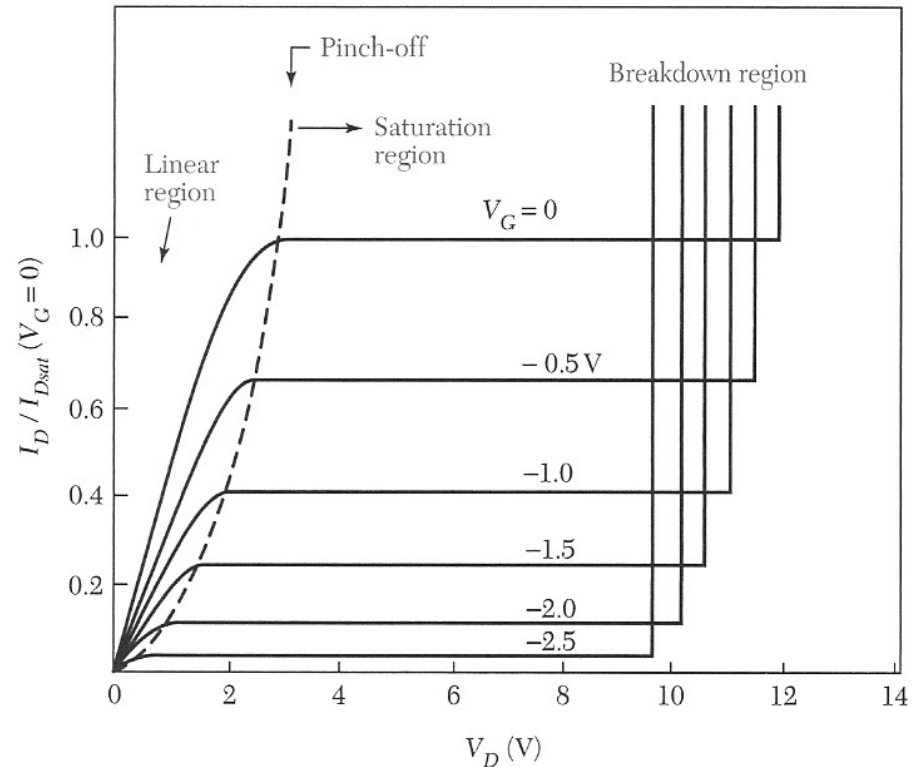
In the saturation regime,

$$I_{sat} = I_p \left[\frac{1}{3} - \frac{V_{bi} - V_G}{V_p} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$

transconductance (describes how good the voltage controlled current source is)

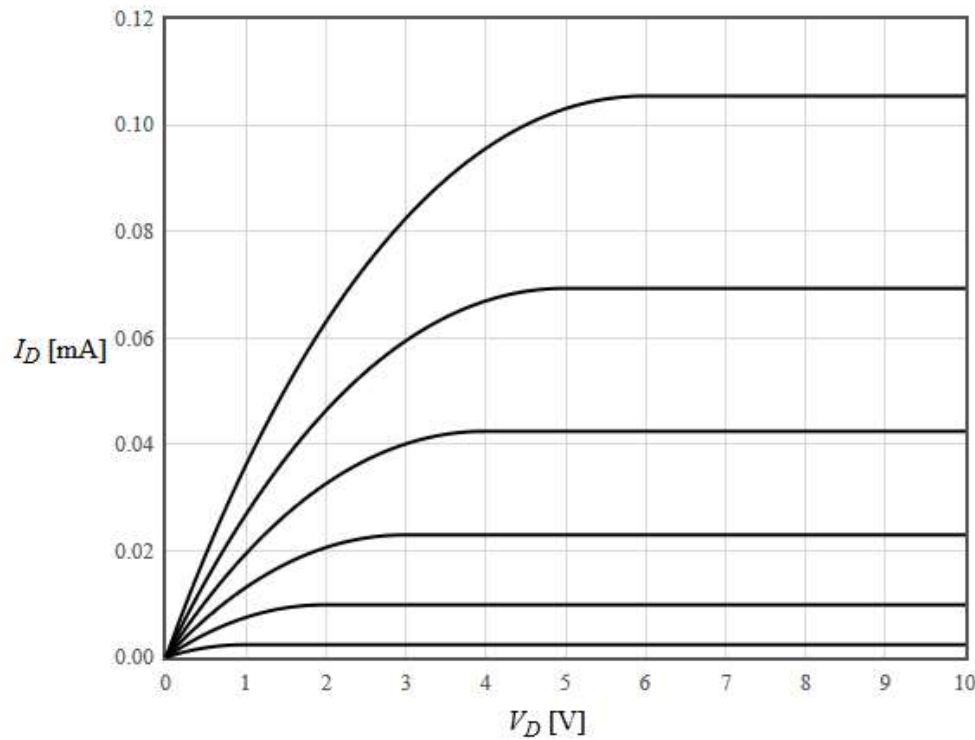
$$g_m = \frac{dI_{sat}}{dV_G} = \frac{I_p}{V_p} \left(1 - \sqrt{\frac{V_{bi} - V_G}{V_p}} \right)$$

$$g_m = \frac{dI_{sat}}{dV_G} = \frac{2Z\mu_n e N_D h}{L} \left(1 - \sqrt{\frac{V_{bi} - V_G}{V_p}} \right)$$



JFET

$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$



$N_c(300K)$	2.78E19	cm ⁻³
$N_v(300K)$	9.84E18	cm ⁻³
E_g	1.166-4.73E-4*T*T/(T+636)	eV
N_D	1E15	cm ⁻³
N_A	1E19	cm ⁻³
μ_n	1350	cm ² /Vs
h	3	μ m
L	100	μ m
Z	100	μ m
ϵ_r	11.9	
T	300	K
$V_D(\text{max})$	10	V
V_g [1]	0	V
V_g [2]	-1	V
V_g [3]	-2	V
V_g [4]	-3	V
V_g [5]	-4	V
V_g [6]	-5	V

Replot

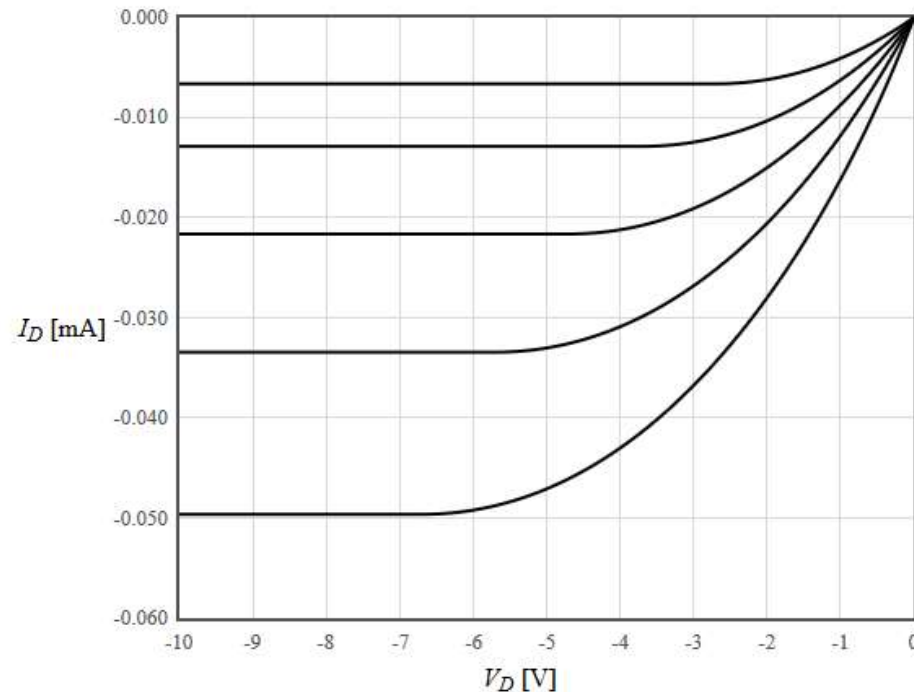
Si Ge GaAs

$E_g = 1.12$ eV; $n_i = 6.41e+9$ cm⁻³; $V_{bi} = 0.856$ V; $I_p = 0.000444$ A; $V_p = 6.84$ V.

p-channel JFET

The expression for the drain current of a p-channel JFET in the linear regime is,

$$I_D = I_p \left[\frac{V_D}{V_p} - \frac{2}{3} \left(\frac{V_{bi} + V_D - V_G}{V_p} \right)^{3/2} + \frac{2}{3} \left(\frac{V_{bi} - V_G}{V_p} \right)^{3/2} \right]$$



$N_c(300K)$	<input type="text" value="2.78E19"/>	cm ⁻³
$N_v(300K)$	<input type="text" value="9.84E18"/>	cm ⁻³
E_g	<input type="text" value="1.166-4.73E-4*T*T/(T+636)"/>	eV
N_D	<input type="text" value="1E19"/>	cm ⁻³
N_A	<input type="text" value="1E15"/>	cm ⁻³
μ_p	<input type="text" value="480"/>	cm ² /Vs
h	<input type="text" value="3"/>	μm
L	<input type="text" value="100"/>	μm
Z	<input type="text" value="100"/>	μm
ϵ_r	<input type="text" value="11.9"/>	
T	<input type="text" value="300"/>	K
$V_D(\text{min})$	<input type="text" value="-10"/>	V
$V_g [1]$	<input type="text" value="0"/>	V
$V_g [2]$	<input type="text" value="1"/>	V
$V_g [3]$	<input type="text" value="2"/>	V
$V_g [4]$	<input type="text" value="3"/>	V
$V_g [5]$	<input type="text" value="4"/>	V
$V_g [6]$	<input type="text" value="5"/>	V

Replot

Si Ge GaAs

$E_g = 1.12 \text{ eV}; \quad n_i = 6.41 \times 10^9 \text{ cm}^{-3}; \quad V_{bi} = 0.856 \text{ V}; \quad I_p = -0.000158 \text{ A}; \quad V_p = -6.84 \text{ V}.$

High frequencies

$$\tilde{i}_{in} = 2\pi f C_G \tilde{v}_G$$

$$\tilde{i}_{out} = g_m \tilde{v}_G$$

for gain: $\tilde{i}_{in} < \tilde{i}_{out}$

$$f < \frac{g_m}{2\pi C_G} = f_T$$

f_T is the frequency
where the gain drops
below 1

average capacitance:

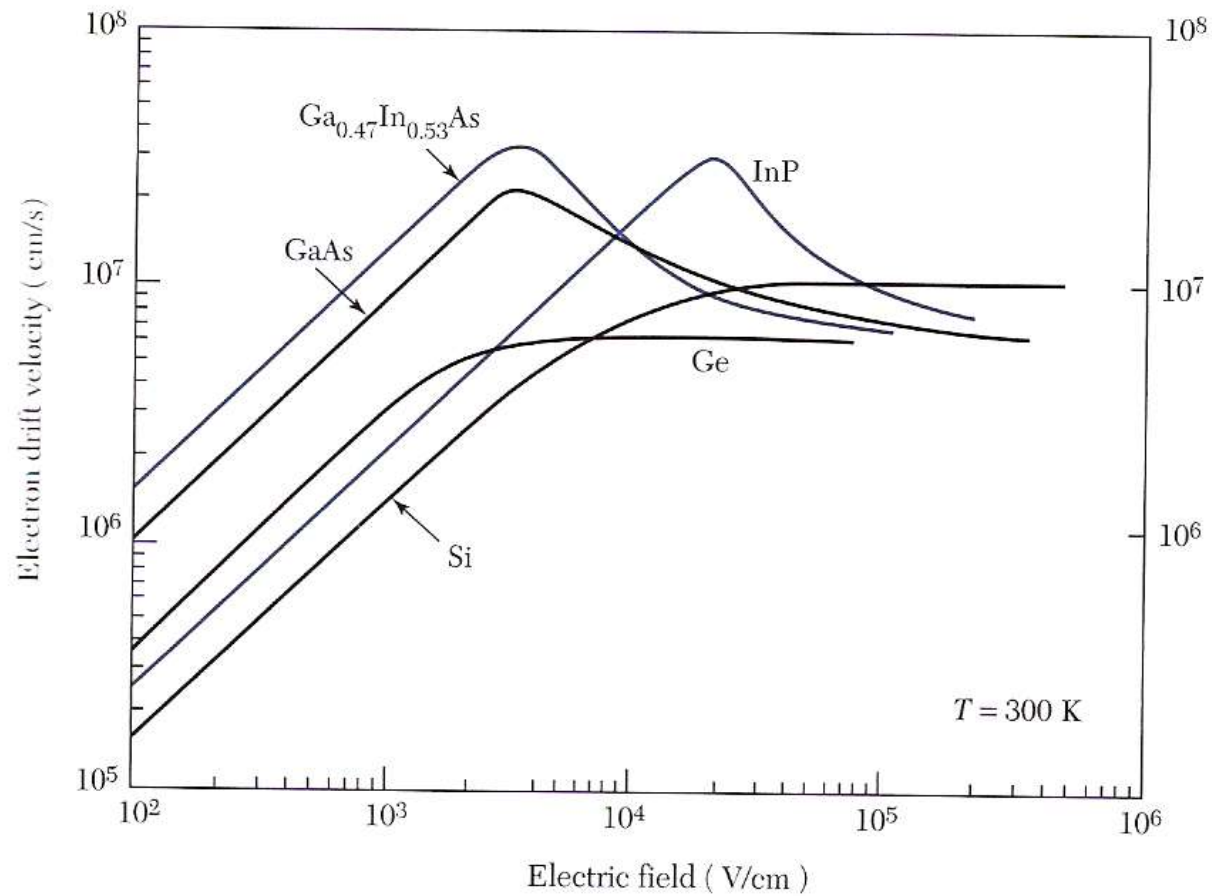
$$C_G = ZL \frac{\epsilon}{\bar{x}_n}$$

$$f_T = \frac{\mu_n e N_D h^2}{2\pi \epsilon L^2}$$

For velocity saturation, the approximation $dV = I_D \frac{\rho dy}{Z(h - x_n(y))}$ is not valid

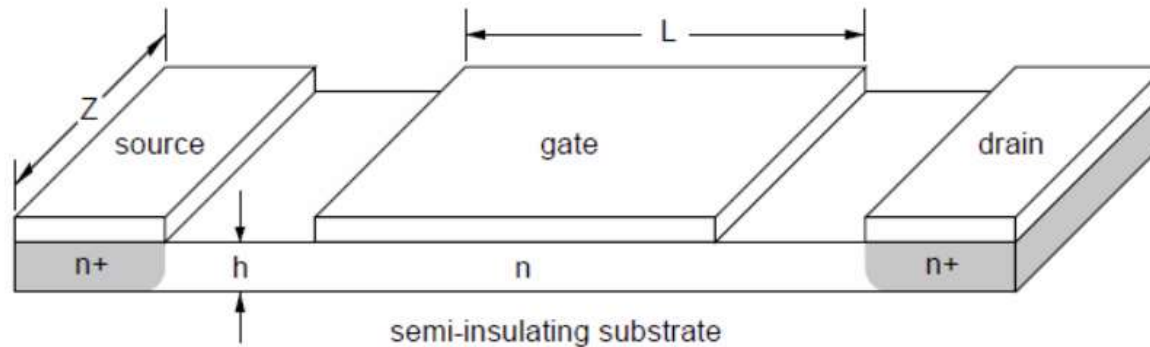
Ohm's law assumes $v_d = \mu E$

$$f_T \approx \frac{v_s}{L}$$

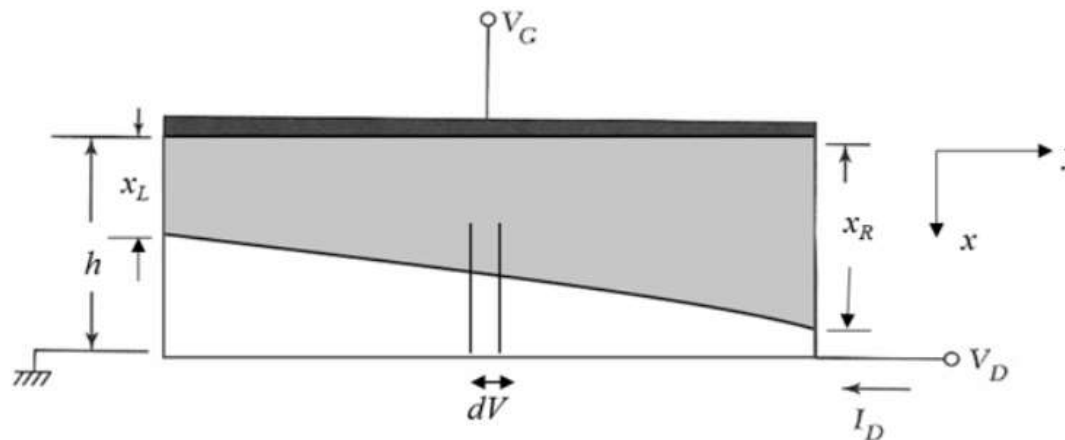


MESFET Gradual Channel Approximation

The description of a MESFET in the gradual channel approximation is almost the same as for a JFET. The difference is how the built-in voltage V_{bi} is calculated. Consider an n -channel MESFET.



A MESFET consists of a semiconducting channel contacted by two ohmic contacts. The metal gate forms a Schottky contact above the channel. The current in the channel flows between the depletion layer of the Schottky diode and a semi-insulating substrate. When the Schottky contact is reverse biased, the depletion width expands and the channel becomes narrower. The thickness of the conducting channel is $h - x_n(y)$ where h is the thickness of the n -doped channel and $x_n(y)$ is the depletion width that depends on the position y along the channel. In the figure below, the gray region of the channel is depleted.



JFET/MESFET

JFET: small gate current (reverse leakage of the gate-to-channel junction)

More gate leakage than MOSFET, less than bipolar.

JFET has higher transconductance than the MOSFET.

Used in low-noise, high input-impedance op-amps and sometimes used in switching applications.

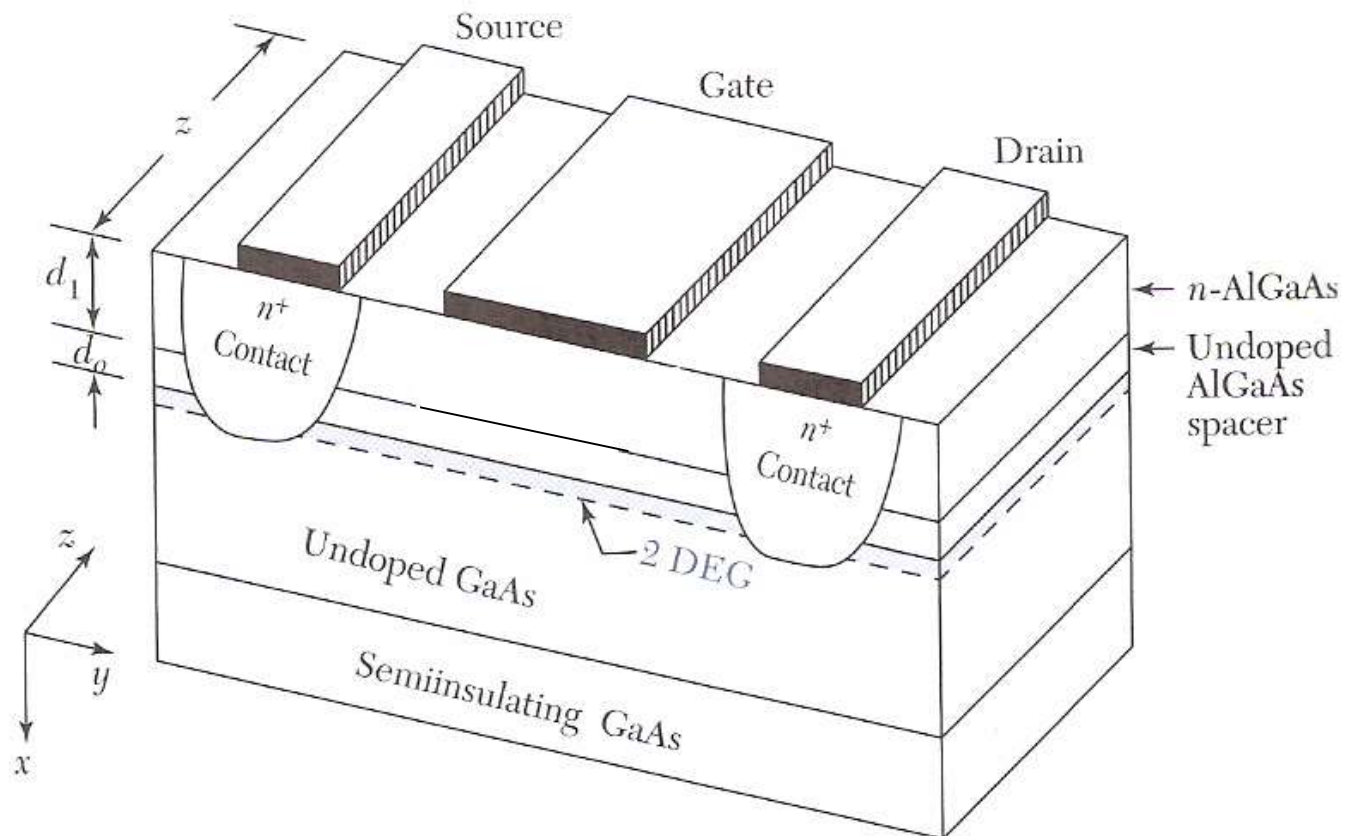
MESFET: usually constructed in compound semiconductor technologies lacking high quality surface passivation such as GaAs, InP, or SiC, and are faster but more expensive than silicon-based JFETs or MOSFETs.

Production MESFETs are operated up to approximately 30 GHz, and are commonly used for microwave frequency communications and radar.

Majority carrier device (like Schottky diode).

MODFET (HEMT)

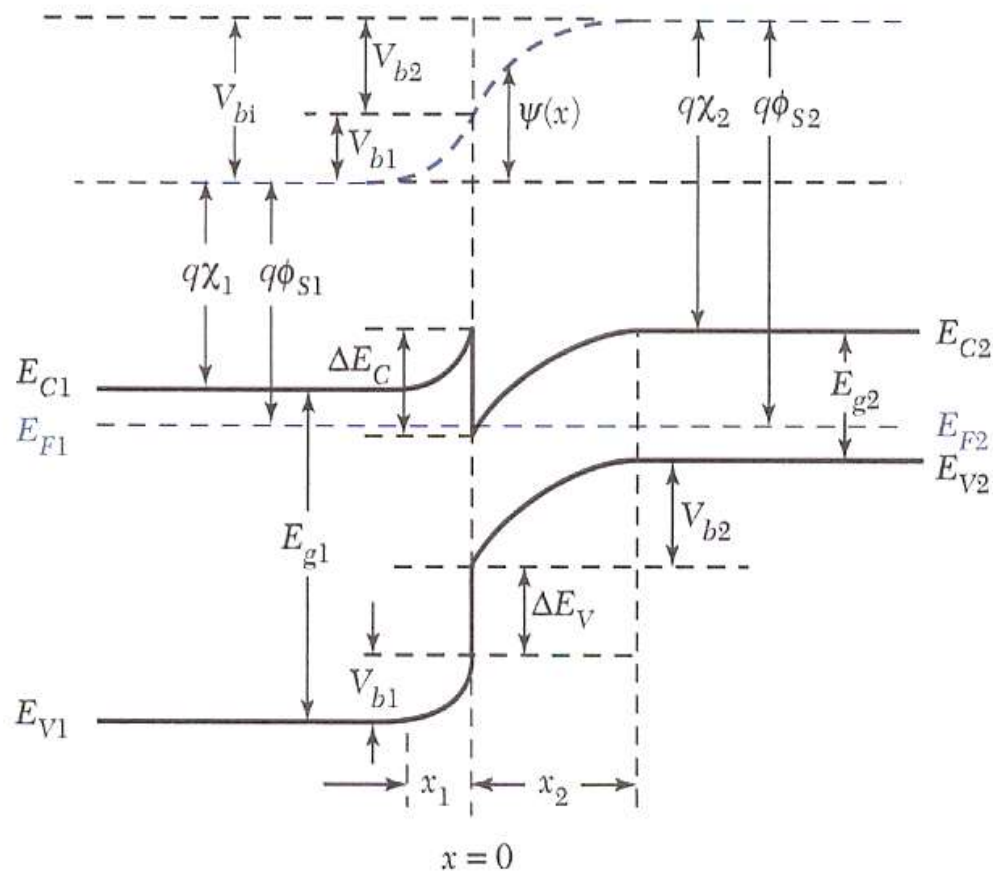
Modulation doped field effect transistor (MODFET)
High electron mobility transistor (HEMT)



V_T = Threshold voltage = voltage where charge is depleted

Heterostructure

pn junction formed from two semiconductors with different band gaps



MODFET (HEMT)

$$j = nev_d = ne\mu_n E_y$$

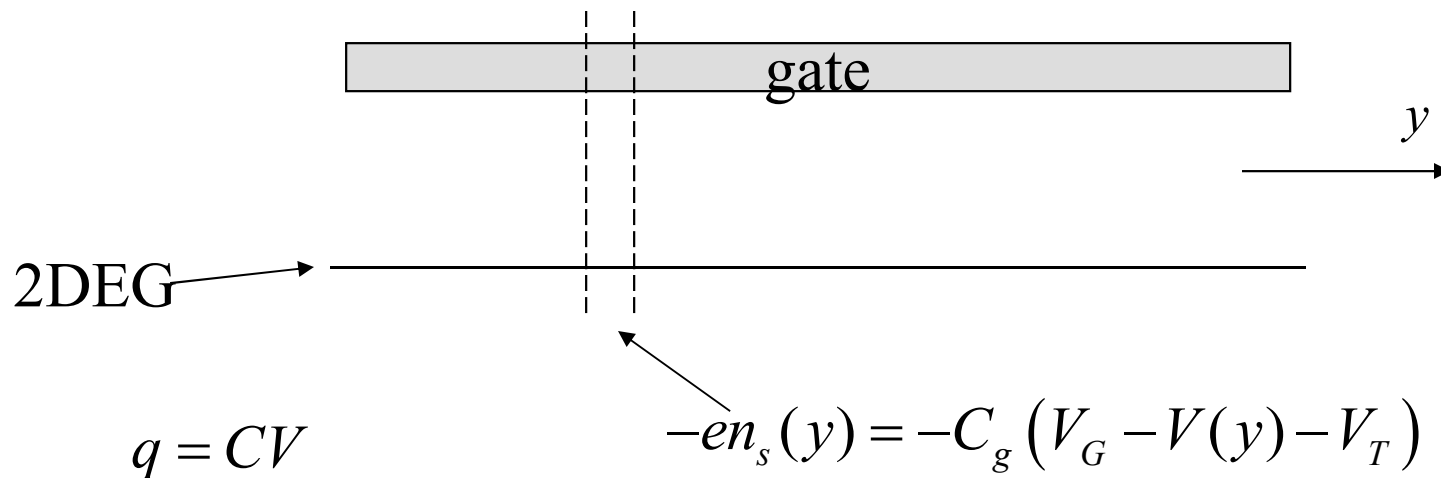
$$I = jZt = Ze\mu_n n_s E_y \quad n = \frac{n_s}{t}$$

t is the thickness of the 2DEG

n_s is the sheet charge at the interface in C/cm².

$V_G - V(y)$ is the voltage between the gate and the 2DEG

$$n_s = 0 \text{ when } V_G - V(y) = V_T$$



MODFET (HEMT)

$-en_s(y) = C_g (V_G - V_B(y) - V_T)$ is the charge on the 2DEG at point y

The charge is zero when $V_G - V_B(y) = V_T$

solve for n_s

$$n_s(y) = \frac{-C_g (V_G - V_B(y) - V_T)}{e}$$

Substitute this in Ohm's law:

$$I = jZt = Ze\mu_n n_s E_y$$

MODFET (HEMT)

$$I = jZt = Ze\mu_n n_s E_y$$

$$n_s(y) = \frac{-C_g (V_G - V(y) - V_T)}{e}$$

substitute n_s in the top equation and substitute

$$E_y = \frac{-dV(y)}{dy}$$

$$I = Z\mu_n C (V_G - V_T - V(y)) \frac{dV(y)}{dy}$$

integrate along the length of the channel

$$\int_0^L I dy = \int_0^{V_D} Z\mu_n C (V_G - V_T - V(y)) dV$$

$$I_D = \frac{Z}{L} \mu_n C \left[(V_G - V_T) V_D - \frac{V_D^2}{2} \right]$$

MODFET (HEMT)

$$I = \frac{Z}{L} \mu_n C \left[(V_G - V_T) V_D - \frac{V_D^2}{2} \right]$$

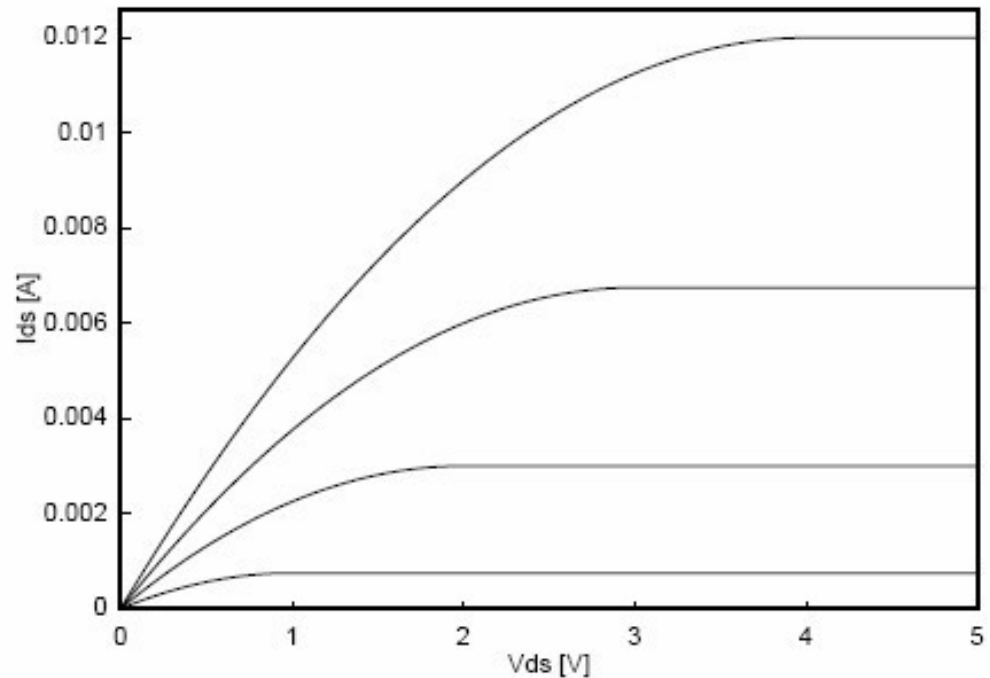
$$\frac{dI}{dV_D} = \frac{Z}{L} \mu_n C \left[(V_G - V_T) - V_D \right] = 0$$

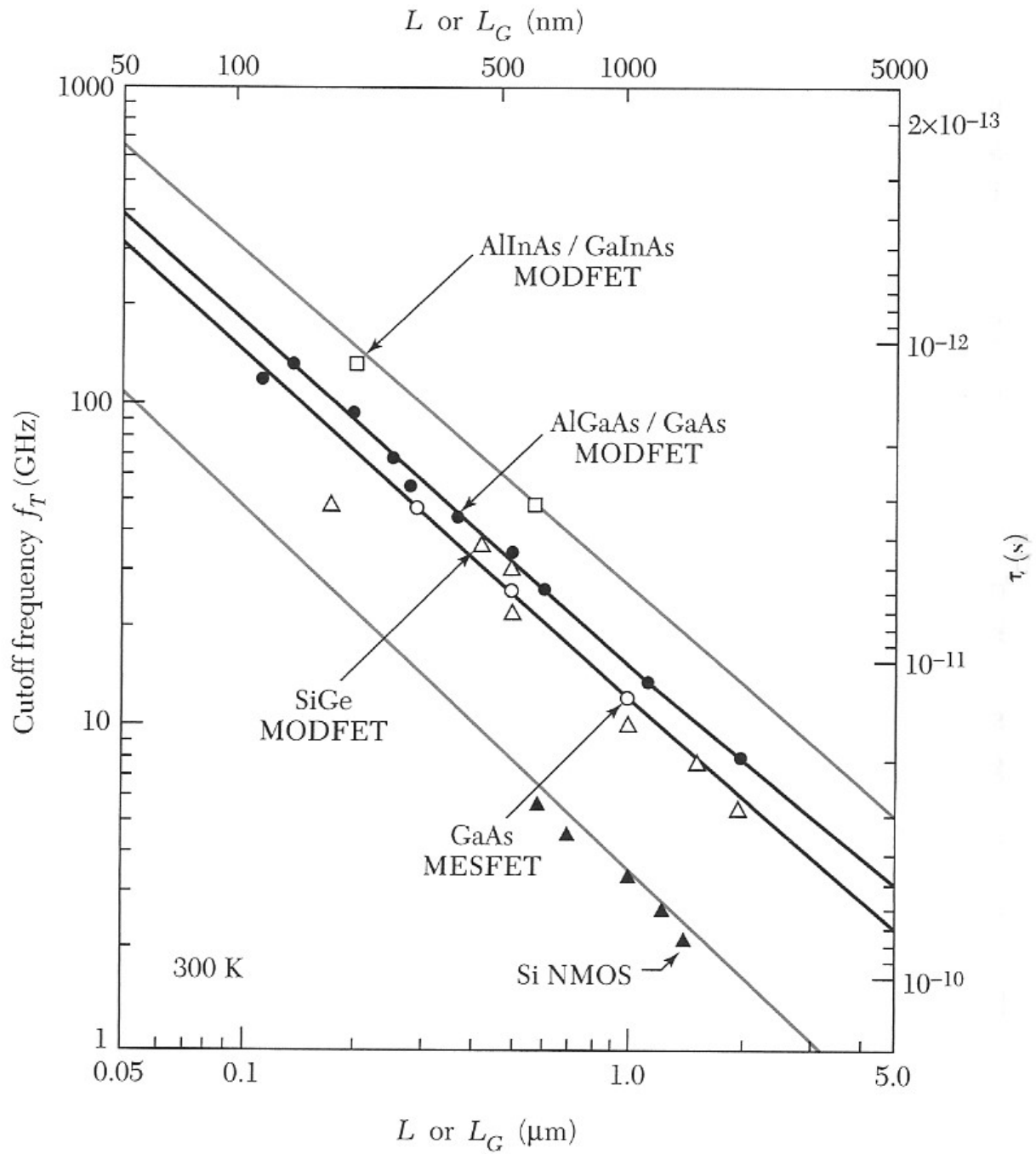
Set the derivative = 0 to find saturation voltage

$$V_{sat} = (V_G - V_T)$$

Substitute the saturation voltage into the formula at the top to find saturation current

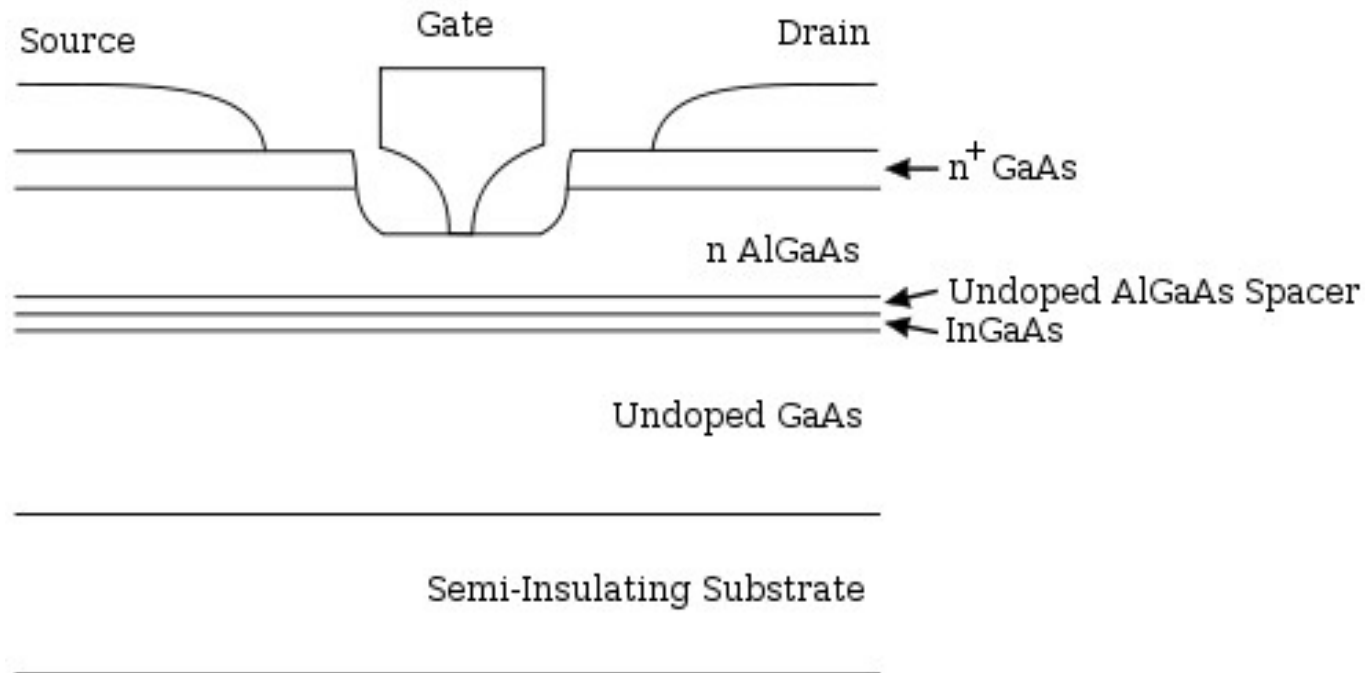
$$I_{sat} = \frac{Z}{2L} \mu_n C (V_G - V_T)^2$$





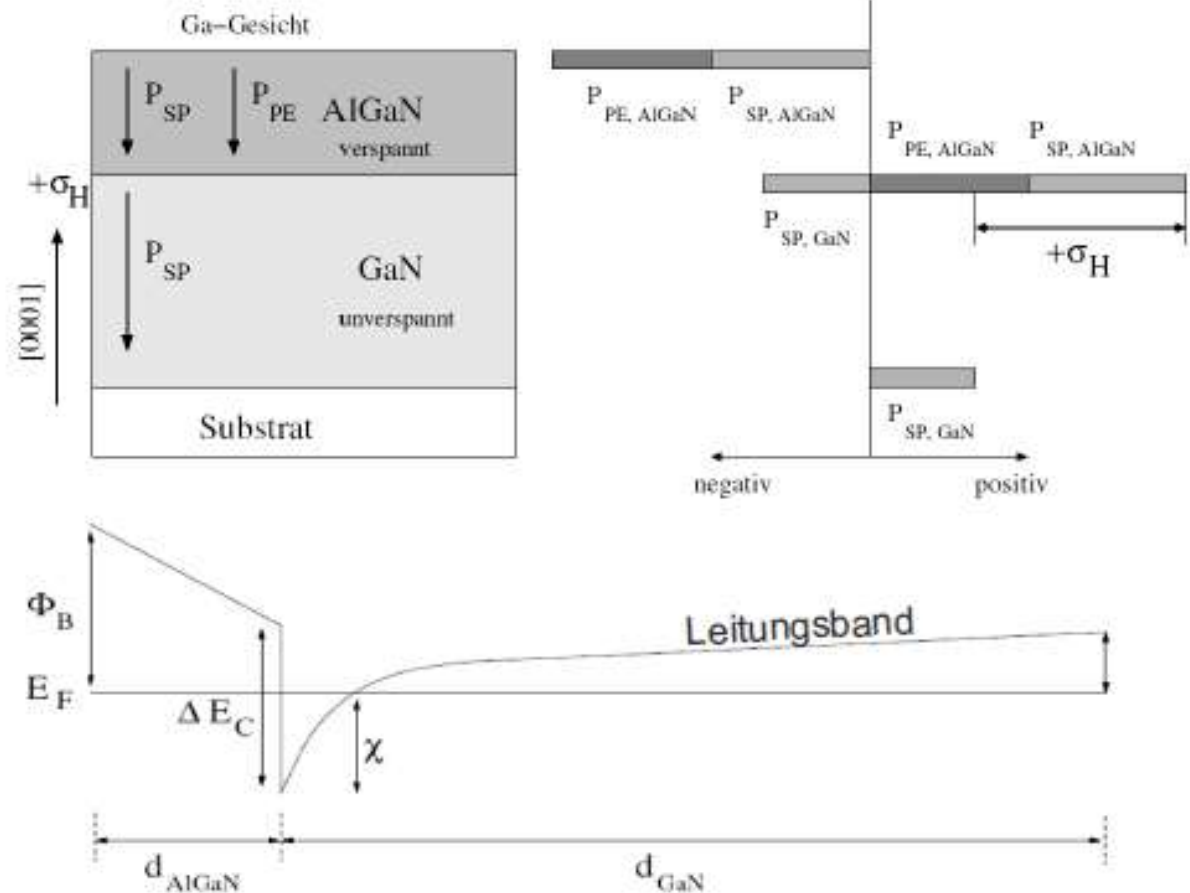
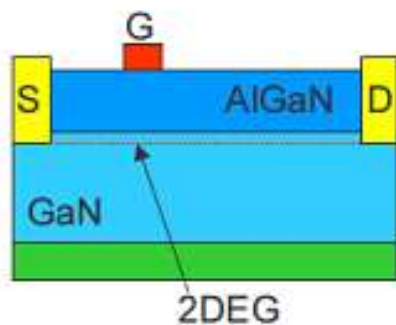
MODFET/HEMT

HEMT: HEMT devices are found in many types of equipment ranging from cell phones and DBS receivers to electronic warfare systems, microwave and millimeter wave communications, radar, and radio astronomy. 600 GHz



GaN-HEMT

- ▶ $E_g(\text{GaN}) = 3.4 \text{ eV}$
- ▶ $E_g(\text{AlGaN}) = 3.5 \dots 6 \text{ eV}$
- ▶ $P_{\text{SP}}(\text{AlGaN}) > P_{\text{SP}}(\text{GaN})$
- ▶ AlGaN wächst zug-verspannt auf GaN
- ▶ AlGaN hat P_{PE}
- ▶ Sprung in P erzeugt Flächenladung
- ▶ \rightarrow 2DEG



Source: Oliver Hilt, „Bauteile aus GaN“, ETG Tagung Bad Nauheim 2011

MOSFETs

Metal Oxide Semiconductor
Field Effect Transistor